IXYS

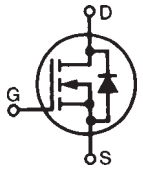
Advance Technical Information

X4-Class Power MOSFET™

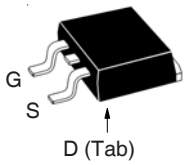
IXTA130N15X4
IXTA130N15X4-7

V_{DSS} = 150V
I_{D25} = 130A
$R_{DS(on)}$ ≤ 8.0mΩ

N-Channel Enhancement Mode
Avalanche Rated

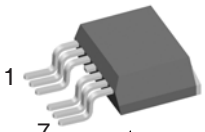


TO-263 AA



G = Gate D = Drain
S = Source Tab = Drain

TO-263 (7-Leads)



Pins: 1 - Gate
2, 3, 5 , 6 , 7 - Source
4 (Tab) - Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	150	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	150	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	130	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	240	A
I_A	T_C = 25°C	65	A
E_{AS}	T_C = 25°C	800	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	10	V/ns
P_D	T_C = 25°C	400	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
F_C	Mounting Force	10.65 / 2.2..14.6	N/lb
Weight	TO-263	2.5	g
	TO-263 (7Leads)	3.0	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	150			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	2.5		4.5	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			5	μA
	T_J = 125°C			200	μA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Notes 1&2		7.0	8.0	mΩ

Features

- International Standard Packages
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
g_{fs}	V_{DS} = 10V, I_D = 60A, Note 1	70	120		S
R_{Gi}	Gate Input Resistance		3.4		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		4770		pF
C_{oss}			710		pF
C_{rss}			3.5		pF
	Effective Output Capacitance				
$C_{o(er)}$	Energy related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		560		pF
$C_{o(tr)}$	Time related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		1850		pF
$t_{d(on)}$	**Resistive Switching Times**		20		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		27		ns
$t_{d(off)}$	R_G = 5Ω (External)		100		ns
t_f			10		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		87		nC
Q_{gs}			24		nC
Q_{gd}			23		nC
R_{thJC}				0.31	°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
I_S	V_{GS} = 0V			130	A
I_{SM}	Repetitive, pulse Width Limited by T_{JM}			520	A
V_{SD}	I_F = 100A, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 65A, -di/dt = 100A/μs		93		ns
Q_{RM}	V_R = 75V		310		nC
I_{RM}			6.7		A

Notes: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

Fig. 1. Output Characteristics @ T_J = 25°C

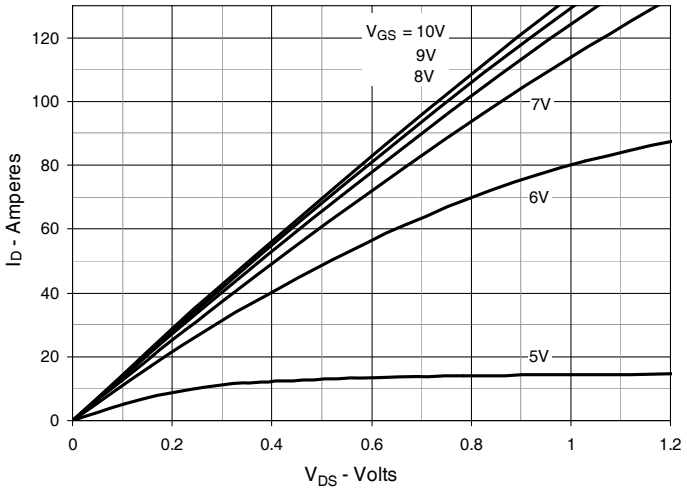


Fig. 2. Extended Output Characteristics @ T_J = 25°C

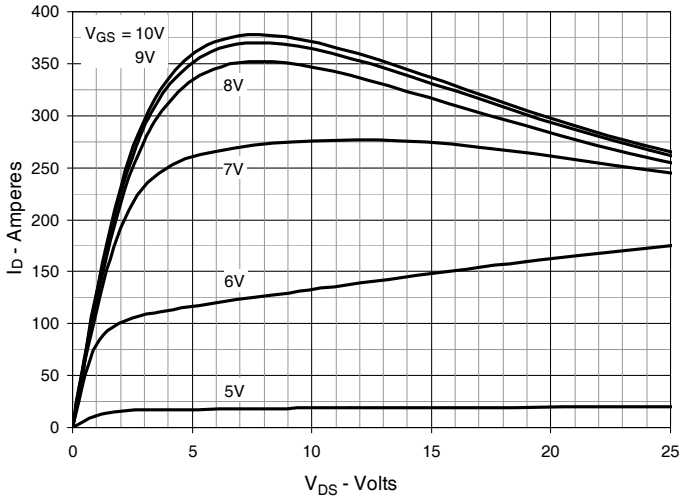


Fig. 3. Output Characteristics @ T_J = 125°C

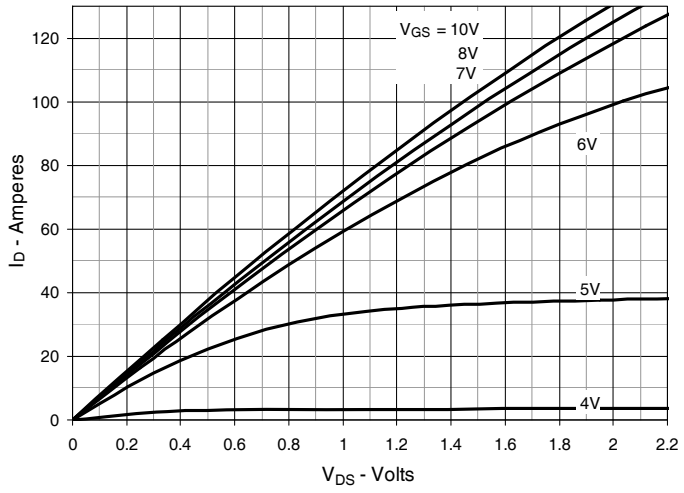


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 65A Value vs. Junction Temperature

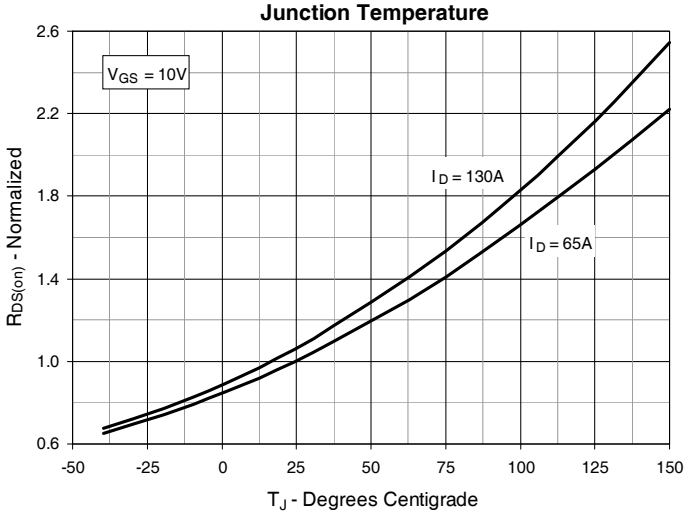


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 65A Value vs. Drain Current

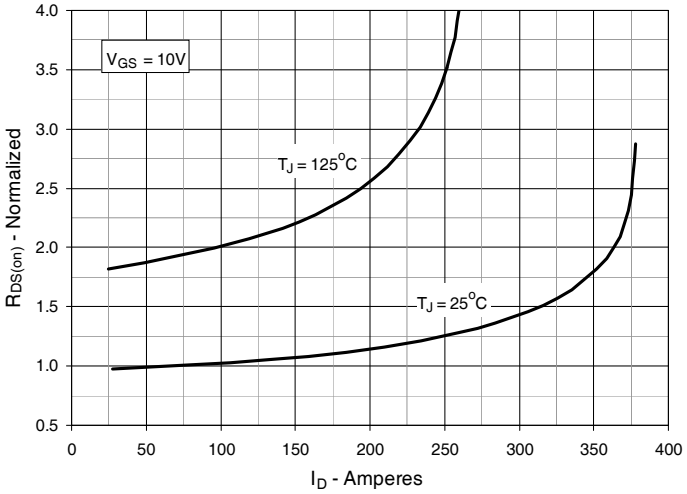


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

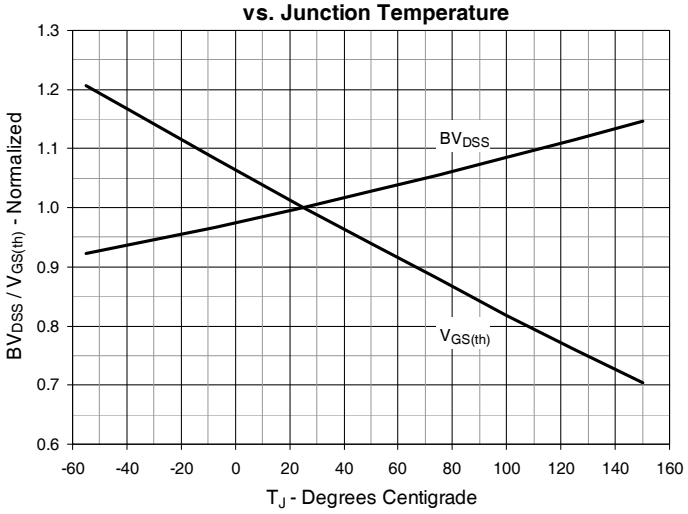


Fig. 7. Maximum Drain Current vs. Case Temperature

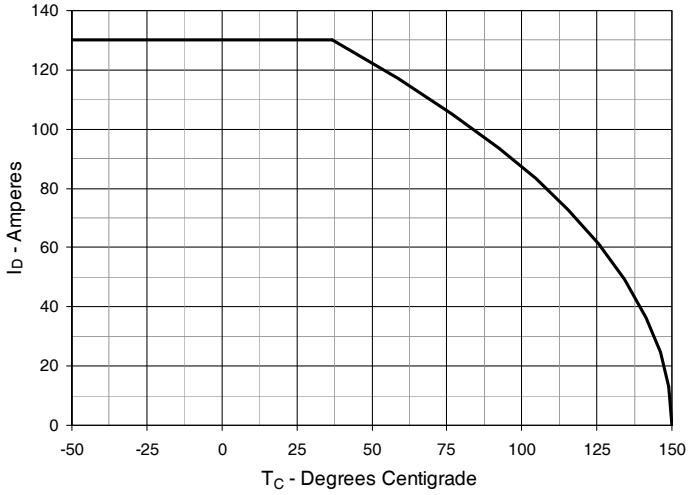


Fig. 8. Input Admittance

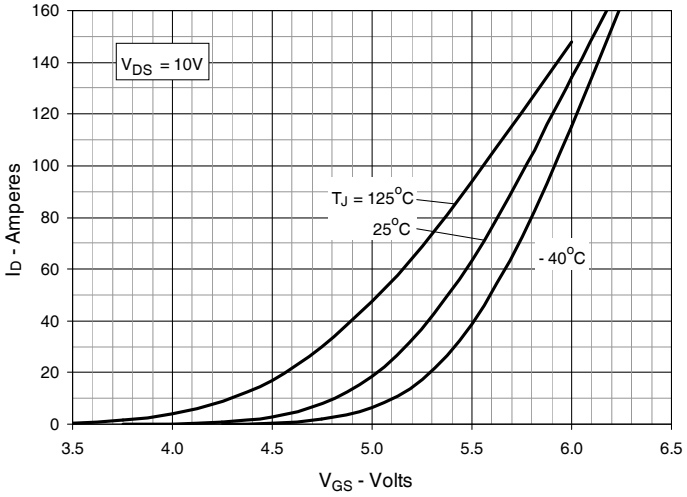


Fig. 9. Transconductance

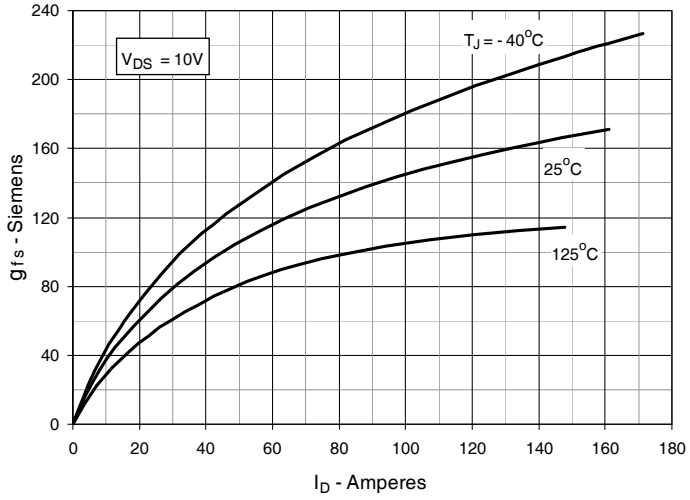


Fig. 10. Forward Voltage Drop of Intrinsic Diode

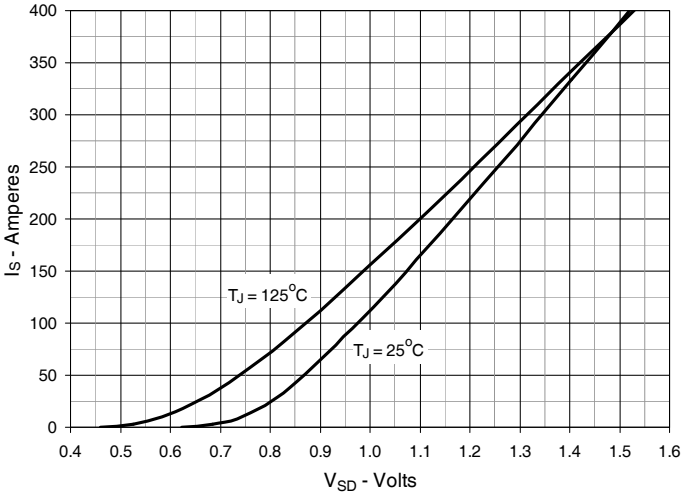


Fig. 11. Gate Charge

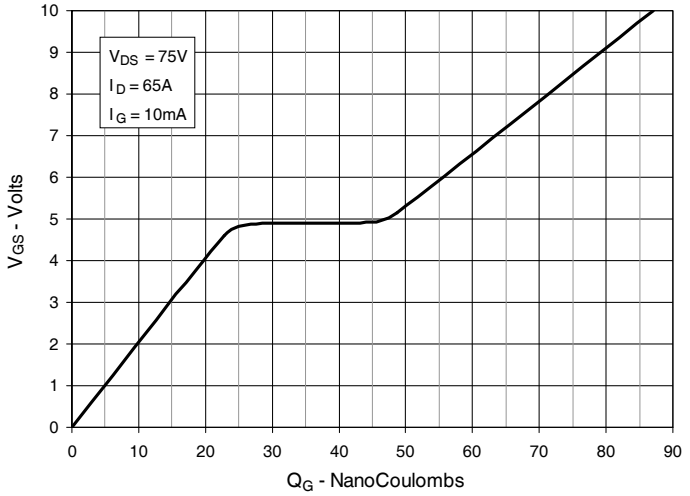


Fig. 12. Capacitance

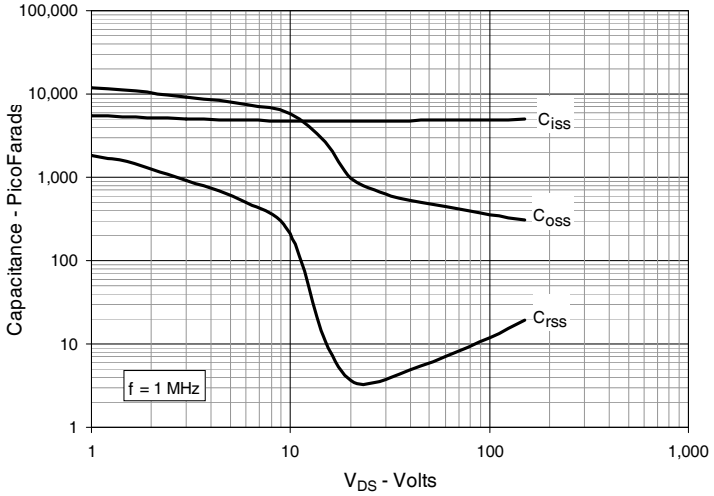


Fig. 13. Output Capacitance Stored Energy

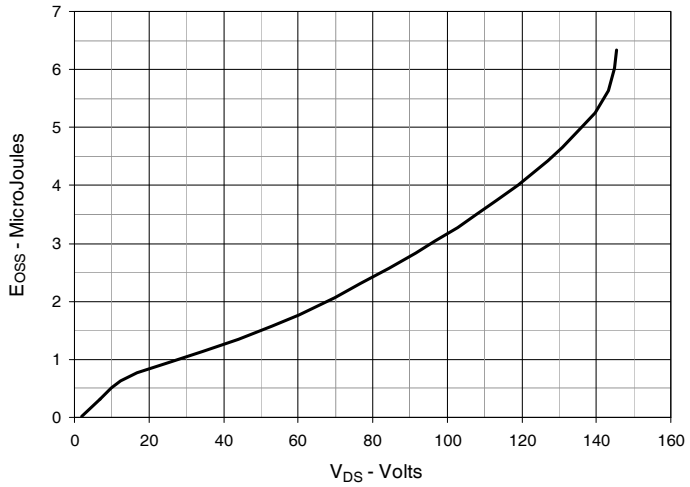


Fig. 14. Forward-Bias Safe Operating Area

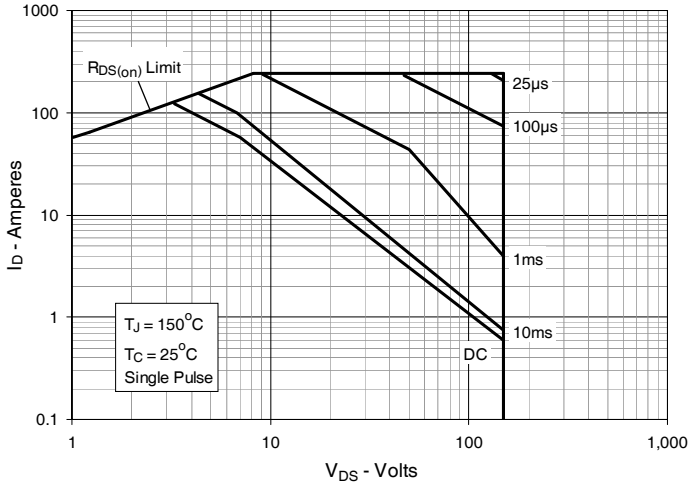
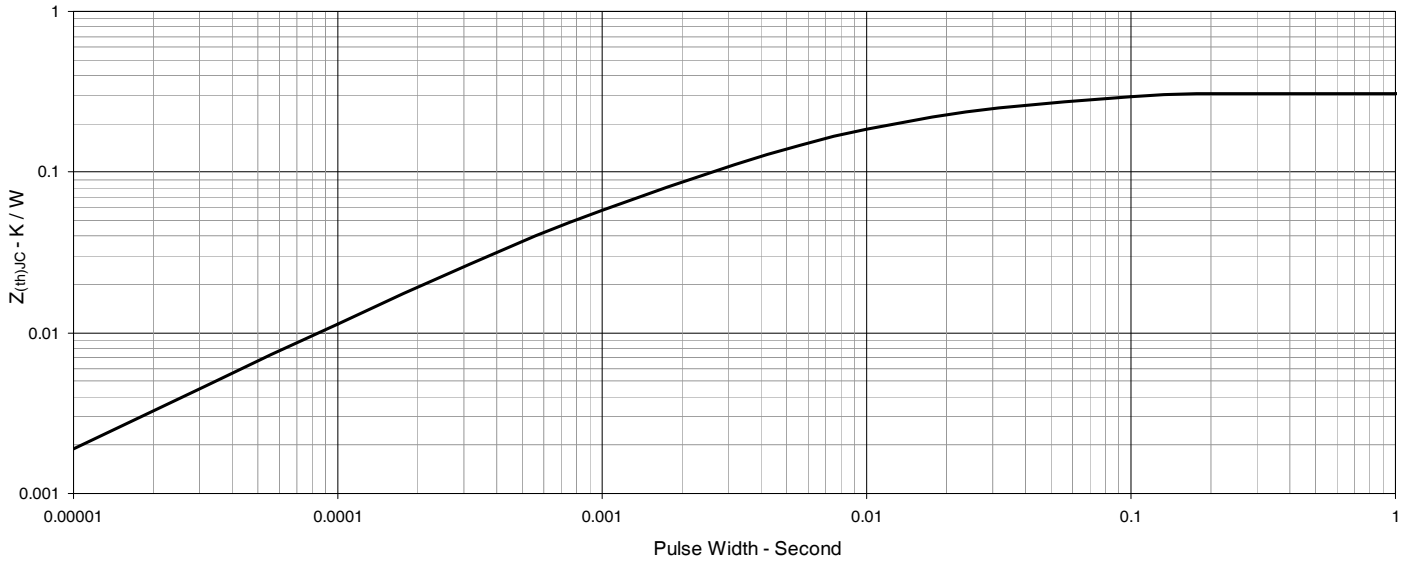
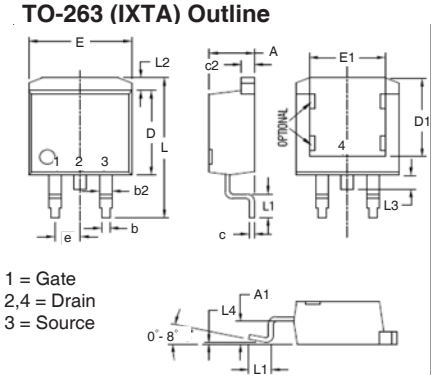


Fig. 15. Maximum Transient Thermal Impedance



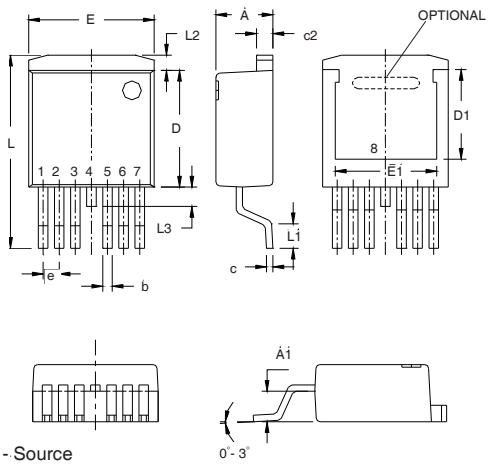
TO-263 (IXTA) Outline



1 = Gate
2,4 = Drain
3 = Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-263 (7-lead) (IXTA..7) Outline



Pins: 1 - Gate
2,3,5,6,7 - Source
4, 8 - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050 BSC		1.27BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50